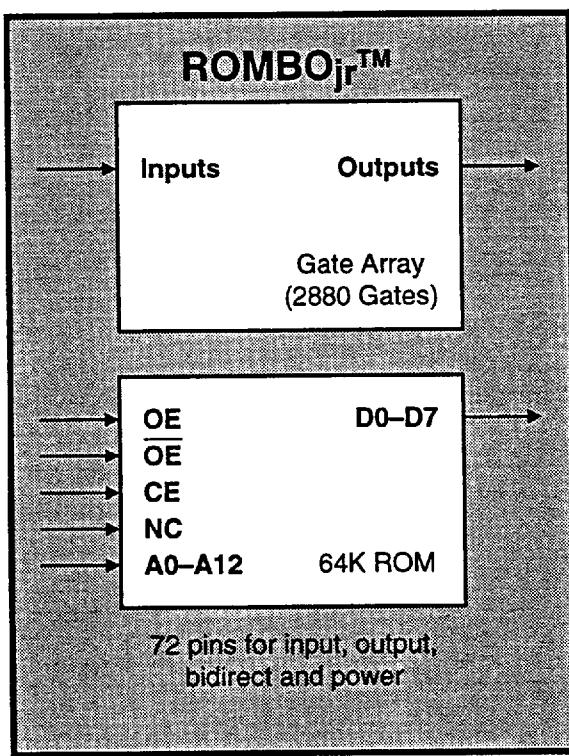


Low Power, High Performance CMOS Gate Array and ROM Combo**Features**

- 64K ROM: 8192 words x 8 bits
- 2880 available gates, 2000 usable gates
- 3V or 5V operating supply
- 90ns access time from Address
- Auto low power standby mode in ROM
- Typical gate delay = 300ps, fanout = 2
- Programmable ROM Enable active level
- Output buffers programmable, from 2mA to 24mA
- Low Power ROM: 2mA Operating, 50 µA Standby
- Input levels selectable, CMOS, TTL, ECL, hysteresis, Analog Comparator
- 74 pads; each can be assigned as power, GND, Input, Output, or I/O
- Latch-Up immunity on all pins
- Class 3 (4000V) ESD Protection
- Wide range of packaging options
Plastic or Ceramic DIP
PQFP and TQFP
PLCC, TSOP

**Figure 1. ROMBO Block Diagram**

Absolute Maximum Ratings: Voltages with respect to ground (V_{ss}) unless otherwise noted.

| Parameter | Symbol | Min. | Max. | Units |
|-----------------------|-----------|------|----------------|-------|
| Supply Voltage | V_{DD} | | 7.0 | V |
| Input Voltage | V_I | -0.5 | $V_{DD} + 0.5$ | V |
| Output Voltage | V_O | -0.5 | $V_{DD} + 0.5$ | V |
| Operating Temperature | T_{OP} | 0° | 85° | C |
| Storage temperature | T_{STG} | -25° | 125° | C |

NOTE: Exceeding these values may cause permanent damage. Functional operation under these conditions is not implied. Functional operation should be restricted to the conditions described under Recommended Operating Conditions.

Recommended Operating Conditions: Voltages with respect to ground (V_{ss}) unless otherwise noted.

| Characteristics | Symbol | Test Conditions | Min. | Max. | Units |
|---|-----------|-----------------------|------|------|---------|
| Supply Voltage | V_{DD} | | 4.75 | 5.25 | V |
| Supply current (static) ^(1, 2) | I_{DD1} | No D.C. loads on pads | | 50 | μA |
| Supply current (static) ^(1, 3) | I_{DD2} | No D.C. loads on pads | | 2 | mA |
| Ambient Temperature | T_A | | 0° | 70° | C |

NOTE 1: All other inputs are connected to V_{DD} or V_{ss} while measuring I_{DD} .

NOTE 2: I_{DD1} is measured with the internal ROM inactive.

NOTE 3: I_{DD2} is measured with the internal ROM inactive, CS, OE, and CE in active state.

DC Characteristics: Voltages with respect to ground (V_{ss}) unless otherwise noted.

Specified at $V_{DD} = 5V \pm 5\%$, ambient temperature 0 to 70°C.

| Input Characteristics | Symbol | Conditions | Min. | Typ. | Max. | Units |
|----------------------------------|-----------|-------------------------------|--------------|------|--------------|---------|
| Input voltage range | V_{IN} | | $V_{ss}-0.5$ | | $V_{DD}+0.5$ | V |
| Hysteresis, High Threshold | V_T+ | | 2.35 | | 2.90 | V |
| Hysteresis, Low Threshold | V_T- | | 1.85 | | 2.45 | V |
| Hysteresis, $V_T+ - V_T-$ | DV_T | | 0.35 | 0.50 | 0.60 | V |
| TTL, Input high | V_{IH} | | 2.0 | | | V |
| TTL, Input low | V_{IL} | | | | 0.8 | V |
| ECL, Diff. input range | V_{IDR} | | 350 | | | mV |
| ECL, Common mode range | V_{ICR} | | 2.5 | | $V_{DD}-1.0$ | V |
| CMOS, Input high | V_{IH} | | 3.5 | | | V |
| CMOS, Input low | V_{IL} | | | | 1.5 | V |
| Comparator Input Common Mode | V_{ICR} | | 1.0 | | $V_{DD}-1.5$ | V |
| Comparator input offset | V_{OS} | | | | 10 | mV |
| Comparator gain | AV | | | 750 | | V/V |
| Pull down current | I_{ID} | $V_{IN} = V_{DD}$ | 3 | 12 | 50 | μA |
| Pull up current | I_{IU} | $V_{IN} = V_{ss}$ | -50 | -12 | -3 | μA |
| Input leakage | I_{IL} | $V_{IN} = V_{DD}$ to V_{ss} | -10 | | +10 | μA |
| Output Characteristics | Symbol | Conditions | Min. | Typ. | Max. | Units |
| CMOS Output Low | V_{OL} | $I_{OL} = 2.0$ to 24 mA | | | 0.4 | V |
| CMOS Output High | V_{OH} | $I_{OH} = -2.0$ to 24 mA | $V_{DD}-1.0$ | | | V |
| TTL Output Low | V_{OL} | $I_{OL} = 2.0$ to 24 mA | | | 0.4 | V |
| TTL Output High | V_{OH} | $I_{OL} = -2.0$ to -24 mA | 2.4 | | | V |
| Leakage current (no pullup-down) | I_{IL} | $V_{IN} = V_{DD}$ to V_{ss} | -10 | | 10 | μA |

AC Electrical Characteristics: Voltages with respect to ground (V_{ss}) unless otherwise stated,
also see timing diagram.

| Timing Parameter | Definition | Min. | Typ. | Max. | Units |
|------------------|---|------|------|------|-------|
| t_{ACE} | Chip enable access time, from \overline{CE} | | 100 | | nsec |
| t_{AA} | Address access time | | 90 | | nsec |
| t_{HZ} | Output high Z delay from \overline{CE} | | | 40 | nsec |
| t_{LZ} | Output Low Z delay from \overline{CE} | 5 | | | nsec |
| t_{PU} | Power up Time from \overline{CE} | 0 | | | nsec |
| t_{PD} | Power down time from \overline{CE} | | | 40 | nsec |

NOTE 1: Load capacitance on all outputs is assumed to be 50pf, unless otherwise specified.

NOTE 2: Rise and fall times of all inputs are assumed to be 5ns or less.

Timing Diagram